

IN THE CLAIMS

Claim 1-19 (Cancelled).

20 (Currently Amended). An integrated circuit comprising:

    a semiconductor structure;  
    a gate formed on said semiconductor structure; and  
    a P-type source and a P-type drain region, said source and drain region including both germanium and a P-type source/drain impurity, said source and drain regions region being strained.

21 (Currently Amended). The circuit of claim 20 wherein the ratio of germanium to P-type source/drain impurity impurities is greater than one to one.

22 (Currently Amended). The circuit of claim 20 wherein the ratio of germanium to P-type source/drain impurity impurities is approximately four to one.

23 (Currently Amended). The circuit of claim 20 wherein said source and drain regions are source and drain extensions. P-type impurities are boron impurities.

24 (Original). The circuit of claim 20 wherein said source/drain region that includes both boron and germanium is a source/drain extension.